REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Delete subgroups 10 and 11 in Table IIA for device class Q. - lgt	00-03-07	R. MONNIN
B	Change made to paragraph 3.2.3. Remove radiation test circuit for device types 01 and 02. – rrp	00-10-13	R. MONNIN
C	Delete case outline Z figure 1. Drawing updated to reflect current requirements. – gt	03-02-28	R. MONNIN
D	For device type 02 only, make change to $I_{OS(+)}$ and $I_{OS(-)}$ test limits as specified under Table I. - ro	05-10-24	R. MONNIN
E	To make the title generic, delete the words “Radiation hardened” from the title block. Add footnote to Table IIB. Delete paragraph 4.4.4.1.1. Add CAGE code 60264. - ro	11-06-22	C. SAFFLE

REV																				
SHEET																				
REV	E																			
SHEET	15																			

REV STATUS	REV	E	E	E	E	E	E	E	E	E	E	E	E	E	E	E
OF SHEETS	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14	

PMIC N/A

PREPARED BY
L. G. TRAYLOR

DLA LAND AND MARITIME
COLUMBUS, OHIO 43218-3990
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STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

CHECKED BY
RAJESH PITHADIA

APPROVED BY
RAY MONNIN

DRAWING APPROVAL DATE
99-02-12

REVISION LEVEL
E

MICROCIRCUIT, LINEAR, SINGLE, LOW-INPUT-CURRENT OPERATIONAL AMPLIFIER, EXTERNALLY COMPENSATED, MONOLITHIC SILICON

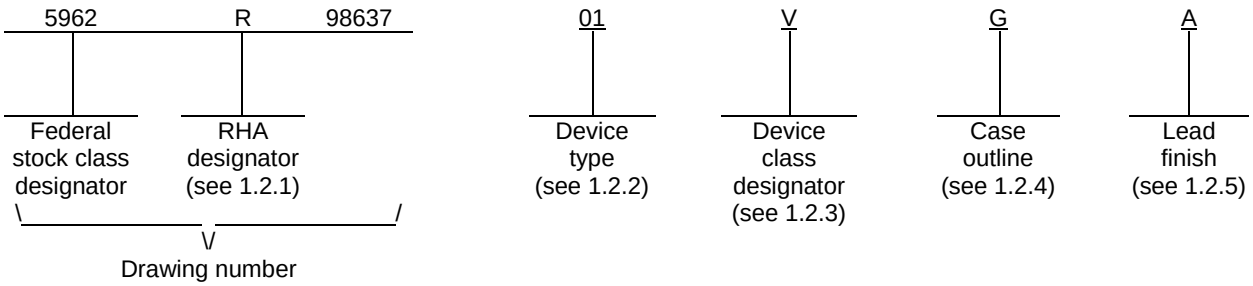
SIZE	CAGE CODE	
A	**67268**	**5962-98637**

SHEET 1 OF 15

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	PM108A	Single low-input-current operational amplifier
02	LM108A	Single low-input-current operational amplifier

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
C	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
G	MACY1-X8	8	Can
H	GDFP1-F10 or CDFP2-F10	10	Flat pack
P	GDIP1-T8 or CDIP2-T8	8	Dual-in-line
Z	GDFP1-G10	10	Flat pack with gull wing leads

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage (V_{CC})	± 22 V
Input voltage (V_{IN}) 2/	± 15 V
Differential input current 3/	± 10 mA
Output short-circuit duration	Indefinite
Storage temperature range	-65°C to +150°C
Lead temperature :	
Device type 01 (soldering, 60 seconds)	300°C
Device type 02 (soldering, 10 seconds)	300°C
Power dissipation (P_D) 4/	500 mW
Thermal resistance, junction-to-case (θ_{JC}) :	
Case C, G, H, P	See MIL-STD-1835
Case Z	21°C/W
Thermal resistance, junction-to-ambient (θ_{JA}) : 5/	
Device type 01:	
Case G	150°C/W
Case H	119°C/W
Case P	119°C/W
Device type 02:	
Case C	94°C/W
Case G	159°C/W
Case H	229°C/W
Case P	123°C/W
Case Z	225°C/W
Junction temperature (T_J)	+175°C

1.4 Recommended operating conditions.

Supply voltage (V_{CC})	±5 V dc to ±20 V dc
Ambient temperature range (T_A)	-55°C to +125°C

1.5 Radiation features.

Maximum total dose available (dose rate = 50 - 300 rads (Si)/s)	100 krads (Si) 6/

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ For supply voltages less than ±15 V, the absolute maximum input voltage is equal to the supply voltage.

3/ The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, if a differential input voltage in excess of 1 V is applied between the inputs, excessive current will flow, unless some limiting resistance is provided.

4/ The maximum power dissipation must be derated at elevated temperatures and is dictated by T_J, θ_{JA}, and T_A. The maximum allowable power dissipation at any temperature is $P_D = (T_J - T_A)/\theta_{JA}$ or the number in 1.3 herein, whichever is lower.

5/ θ_{JA} is specified for worst case mounting conditions, i.e., θ_{JA} is specified for device in socket for TO, CerDIP, and P-DIP packages.

6/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at https://assist.daps.dla.mil/quicksearch/ or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Input offset voltage	V_{IO}	R_S = 50 Ω 4/		1	01	-0.5	0.5	mV
				2, 3		-1.0	1.0	
			M, D, P, L, R	1		-2.0	2.0	
		$+V_{CC}$ = 35 V, $-V_{CC}$ = -5 V, V_{CM} = -15 V		1	02	-0.5	0.5	mV
				2, 3		-1.0	1.0	
			M, D, P, L, R	1		-0.5	0.5	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -35 V, V_{CM} = 15 V		1	02	-0.5	0.5	mV
				2, 3		-1.0	1.0	
			M, D, P, L, R	1		-0.5	0.5	
		$+V_{CC}$ = 20 V, $-V_{CC}$ = 20 V, V_{CM} = 0 V		1	02	-0.5	0.5	mV
				2, 3		-1.0	1.0	
			M, D, P, L, R	1		-0.5	0.5	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -5 V		1	02	-0.5	0.5	mV
				2, 3		-1.0	1.0	
			M, D, P, L, R	1		-0.5	0.5	
Input offset voltage temperature sensitivity	ΔV_{IO} / ΔT	5/ 6/		2, 3	All	-5.0	5.0	µV/°C

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Input offset current	I_{IO}	4/	1	01	-0.2	0.2	nA
			2, 3		-0.4	0.4	
		M, D, P, L, R	1		-1.0	1.0	
		$+V_{CC}$ = 35 V, $-V_{CC}$ = -5 V,	1	02	-0.2	0.2	nA
		V_{CM} = -15 V, R_S = 5 MΩ	2, 3		-0.4	0.4	
		M, D, P, L, R	1			0.5	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -35 V,	1	02	-0.2	0.2	nA
		V_{CM} = 15 V, R_S = 5 MΩ	2, 3		-0.4	0.4	
		M, D, P, L, R	1			0.5	
		R_S = 5 MΩ	1	02	-0.2	0.2	nA
			2, 3		-0.4	0.4	
		M, D, P, L, R	1			0.5	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -5 V,	1	02	-0.2	0.2	nA
		R_S = 5 MΩ	2, 3		-0.4	0.4	
		M, D, P, L, R	1			0.5	
Input offset current temperature sensitivity	$\Delta I_{IO}/\Delta T$	5/ 6/	2, 3	All	-2.5	2.5	pA/°C

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Input bias current	$\pm I_{IB}$	4/	1	01	-0.1	2.0	nA
			2		-1.0	2.0	
			3		-0.1	3.0	
		M, D, P, L, R	1		-25.0	25.0	
		$+V_{CC}$ = 35 V, $-V_{CC}$ = -5 V, V_{CM} = -15 V, R_S = 5 MΩ	1	02	-0.1	2.0	nA
			2		-1.0	2.0	
			3		-0.1	3.0	
		M, D, P, L, R	1			5.0	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -35 V, V_{CM} = 15 V, R_S = 5 MΩ	1	02	-0.1	2.0	nA
			2		-1.0	2.0	
			3		-0.1	3.0	
		M, D, P, L, R	1			5.0	
		R_S = 5 MΩ	1	02	-0.1	2.0	nA
			2		-1.0	2.0	
			3		-0.1	3.0	
		M, D, P, L, R	1			5.0	
		$+V_{CC}$ = 5 V, $-V_{CC}$ = -5 V, R_S = 5 MΩ	1	02	-0.1	2.0	nA
			2		-1.0	2.0	
			3		-0.1	3.0	
		M, D, P, L, R	1			5.0	
Power supply rejection ratio	+PSRR	$+V_{CC}$ = 10 V, R_S = 50 Ω, $-V_{CC}$ = -20 V, 6/	1, 2, 3	All	-16	16	μV/V
	-PSRR	$+V_{CC}$ = 20 V, R_S = 50 Ω, $-V_{CC}$ = -10 V, 6/	1, 2, 3	All	-16	16	μV/V
Input voltage common mode rejection	CMR	V_{CM} = ±15 V 6/	1, 2, 3	All	96		dB

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Adjustment for input offset voltage	V_{IO} ADJ(+)	$\pm V_{CC} = \pm 20$ V 6/	1	01	No external ADJ		mV
Adjustment for input offset voltage	V_{IO} ADJ(-)	$\pm V_{CC} = \pm 20$ V 6/	1	01	No external ADJ		mV
Output short-circuit current (for positive output)	$I_{OS(+)}$	$\pm V_{CC} = \pm 15$ V, 6/ 7/ $t \le 25$ ms	1	01	-15.0		mA
				02	-20.0		
			2, 3	02	-20.0		
Output short-circuit current (for negative output)	$I_{OS(-)}$	$\pm V_{CC} = \pm 15$ V, 6/ 7/ $t \le 25$ ms	1	01		15.0	mA
				02		20.0	
			2, 3	02		20.0	
Supply current	I_{CC}	$\pm V_{CC} = \pm 15$ V 6/	1, 2	All		0.6	mA
			3			0.8	
Output voltage swing (maximum)	$\pm V_{OP}$	$\pm V_{CC} = \pm 20$ V, 6/ $R_L = 10$ kΩ	4, 5, 6	01	-16.0	16.0	V
	$+V_{OP}$	$R_L = 10$ kΩ	4, 5, 6	02	-16.0		V
	$-V_{OP}$	$R_L = 10$ kΩ	4, 5, 6	02		16.0	V
Open loop voltage gain (single ended)	$A_{VS\pm}$	$\pm V_{CC} = \pm 15$ V, 8/	4	01	80		V/mV
		$R_L = 10$ kΩ, $V_{OUT} = \pm 10$ V	5, 6		40		
		M, D, P, L, R	1		10		
	$A_{VS(+)}$	$\pm V_{CC} = \pm 20$ V, 8/	4	02	80		V/mV
		$R_L = 10$ kΩ, $V_{OUT} = +15$ V	5, 6		40		
	$A_{VS(-)}$	$\pm V_{CC} = \pm 20$ V, 8/	4	02	80		V/mV
		$R_L = 10$ kΩ, $V_{OUT} = -15$ V	5, 6		40		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A Subgroups	Device type	Limits		Unit
					Min	Max	
Open loop voltage gain (single ended)	A_{VS}	$\pm V_{CC} = \pm 5$ V, 8/ $R_L = 10$ kΩ, $V_{OUT} = \pm 2$ V	4, 5, 6	02	20		V/mV
Transient response rise time	$TR_{(tr)}$	6/	9	01		1000	ns
		$R_L = 10$ kΩ, $C_L = 100$ pF, $F < 1$ kHz, $V_{IN} = +50$ mV	9, 10, 11	02		1000	ns
Transient response overshoot	$TR_{(OS)}$	6/	9	01		50	%
		$R_L = 10$ kΩ, $C_L = 100$ pF, $F < 1$ kHz, $V_{IN} = +50$ mV	9, 10, 11	02		50	%
Slew rate	SR(+)	$V_{IN} = -5$ V to $+5$ V, 6/ $A_V = 1$	9, 10, 11	01	0.05		V/μs
	SR(-)	$V_{IN} = +5$ V to -5 V, 6/ $A_V = 1$			0.05		
	SR(+)	$V_{IN} = -5$ V to $+5$ V, $A_V = 1$	9, 10, 11	02	0.05		
	SR(-)	$V_{IN} = +5$ V to -5 V, $A_V = 1$			0.05		
Noise (referred to input) broadband	$NI_{(BB)}$	$\pm V_{CC} = \pm 20$ V, 6/ BW = 5 kHz, $T_A = 25°C$	9	01		15	μV rms
	$NI_{(BB)}$	BW = 10 Hz to 5 kHz, $R_S = 0$ Ω, $T_A = 25°C$	9	02		15	μV rms

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ 2/ 3/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A Subgroups	Device type	Limits		Unit
					Min	Max	
Noise (referred to input) popcorn	$NI_{(PC)}$	$\pm V_{CC}$ = 20 V, 6/ BW = 5 kHz, T_A = 25°C	9	01		40	µV pk
		BW = 10 Hz to 5 kHz, R_S = 100 kΩ	9	02		40	µV pk

1/ Devices supplied to this drawing have been characterized through all levels M, D, P, L, R of irradiation. However, this device is only tested at the "R" level. Pre and Post irradiation values are identical unless otherwise specified in table I.

2/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

3/ Unless otherwise specified test conditions include: $V_{CC} = \pm 20$ V, $T_A = 25°C$, $R_S = 50\ \Omega$, $V_{CM} = 0$ V.

4/ Tests at common-mode $V_{CM} = 0$ V, $V_{CM} = -15$ V, and $V_{CM} = +15$ V.

5/ Calculated parameters for device type 02.

6/ This parameter not tested post radiation.

7/ Continuous short-circuit limits will be considerably less than the indicated test limits. Continuous I_{OS} at $T_A \le 75°C$ will cause T_J to exceed the maximum of 175°C.

8/ Note that gain is not specified at $V_{IO(ADJ)}$ extremes. For closed-loop applications (closed-loop gain less than 1000), the open-loop tests (A_{VS}) prescribed herein should guarantee a positive, reasonably linear, transfer characteristic. They do not, however, guarantee that the open-loop gain is linear, or even positive over the operating range. If either of these requirements exist (positive open-loop gain or open-loop gain linearity), they should be specified in the individual procurement document as additional requirements.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

Device types	01, 02		02	
Case outlines	G, P	H	C	Z
Terminal number	Terminal symbol			
1	COMP	NC	NC	NC
2	-IN	NC	COMP	NC
3	+IN	-IN	NC	-IN
4	V-	+IN	-IN	+IN
5	NC	NC	+IN	NC
6	OUT	V-	NC	V-
7	V+	OUT	V-	OUT
8	COMP	V+	NC	V+
9	---	COMP	NC	COMP
10	---	COMP	OUT	COMP
11	---	---	V+	---
12	---	---	COMP	---
13	---	---	NC	---
14	---	---	NC	---

NC = No connection

FIGURE 1. Terminal connections.

3.8 Notification of change for device class M. For device class M, notification to DLA Land and Maritime -VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

3.9 Verification and review for device class M. For device class M, DLA Land and Maritime, DLA Land and Maritime's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 4 1/	1, 2, 3, 4 1/	1, 2, 3, 4 1/ 2/ 3/
Group A test requirements (see 4.4)	1, 2, 3, 4, 5, 6, 9	1, 2, 3, 4, 5, 6, 9	1, 2, 3, 4, 5, 6, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1	1	1, 2, 3 2/ 3/
Group D end-point electrical parameters (see 4.4)	1	1	1, 2, 3
Group E end-point electrical parameters (see 4.4)	---	1	1

1/ PDA applies to subgroup 1.
2/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the previous endpoint electrical parameters.
3/ For device type 02 delta is performed for Group C end point electrical only.

TABLE IIB. 240 hour burn-in and group C end-point electrical parameters. 1/

Test	Device types	Delta	
		Min	Max
V_{IO} 2/	All	-0.25 mV	+0.25 mV
$+I_{IB}$ 2/	All	-0.5 nA	+0.5 nA
$-I_{IB}$ 2/	All	-0.5 nA	+0.5 nA

1/ Deltas are performed at room temperature.
2/ $V_{CC} = \pm 20$ V, $V_{CM} = 0$ V.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

a. Tests shall be as specified in table IIA herein.

b. Subgroups 7 and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table IIA herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019 condition A and as specified herein.

4.4.4.2 Dose rate burnout. When required by the customer test shall be performed on devices, SEC, or approved test structures at technology qualifications and after any design or process changes which may effect the RHA capability of the process. Dose rate burnout shall be performed in accordance with test method 1023 of MIL-STD-883 and as specified herein.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime -VA, telephone (614) 692-0544.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime -VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime -VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DLA Land and Maritime -VA.

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 11-06-22

Approved sources of supply for SMD 5962-98637 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime -VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962R9863701VGA	24355	PM108AJ/QMLR
5962R9863701VPA	24355	PM108AZ/QMLR
5962R9863701VHA	24355	PM108AL/QMLR
5962-9863702QCA	60264	MTLM108AQD
5962-9863702QGA	60264	MTLM108AQH
5962-9863702QPA	60264	MTLM108AQD8
5962R9863702QCA	3/	LM108AJRQML
5962R9863702QGA	3/	LM108AHRQML
5962R9863702QPA	3/	LM108AJ-8RQML
5962R9863702QHA	3/	LM108AWRQML
5962R9863702QZA	3/	LM108AWGRQML
5962R9863702VCA	3/	LM108AJRQMLV
5962R9863702VGA	27014 4/	LM108AHRQMLV
5962R9863702VPA	3/	LM108AJ-8RQMLV
5962R9863702VHA	27014 4/	LM108AWRQMLV
5962R9863702VZA	27014 4/	LM108AWGRQMLV

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
3/ Not available from an approved source of supply.
4/ This device has an end of life date of March 16, 2012.

Vendor CAGE number	Vendor name and address
24355 (4)	Analog Devices Route 1 Industrial Park P.O. Box 9106 Norwood, MA 02062 Point of contact: 7910 Triad Center Drive Greensboro, NC 27409-9605
27014	National Semiconductor 2900 Semiconductor Dr. P.O. Box 58090 Santa Clara, CA 95052-8090
60264	Minco Technology Labs, Inc. 1805 Rutherford Lane Austin, TX 78754-5101